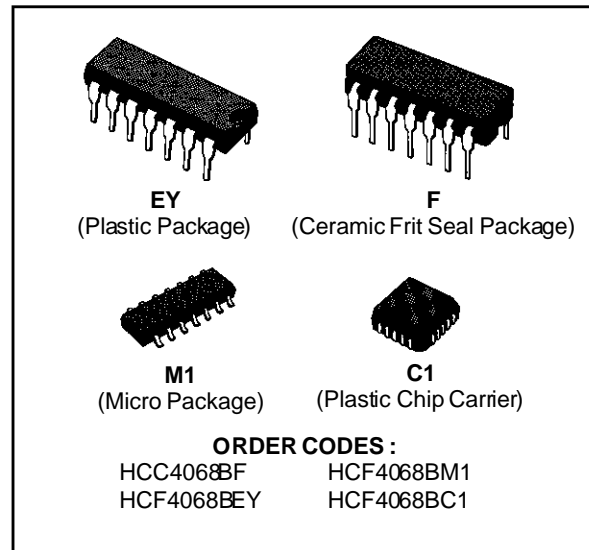


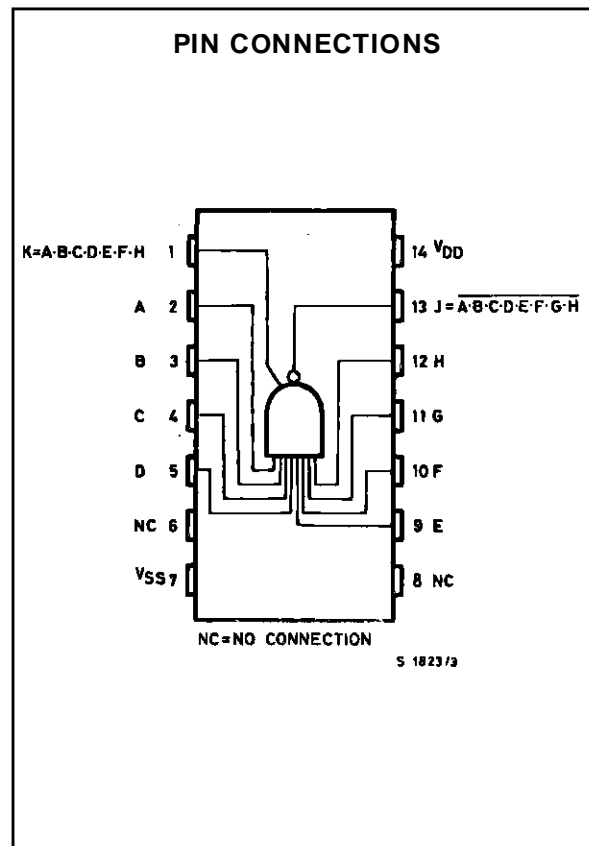
8-INPUT NAND/AND GATE

- MEDIUM-SPEED OPERATION – t_{PHL} , t_{PLH} = 75ns (typ.) AT 10V
- BUFFERED OUTPUT
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



DESCRIPTION

The **HCC4068B** (extended temperature range) and **HCF4068B** (intermediate temperature range) are monolithic integrated circuit, available in 14-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF4068B** NAND/AND gate provides the system designer with direct implementation of the positive-logic 8-input NAND and AND functions and supplements the existing family of COS/MOS gates.



HCC/HCF4068B

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _i	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to 125	°C
		- 40 to 85	°C

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions				Value						Unit		
		V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *			
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.	
I _L	Quiescent Current	HCC Types	0/ 5			5		0.25		0.01	0.25		7.5	μA
			0/10			10		0.5		0.01	0.5		15	
			0/15			15		1		0.01	1		30	
			0/20			20		5		0.02	5		150	
		HCF Types	0/ 5			5		1		0.01	1		7.5	
			0/10			10		2		0.01	2		15	
			0/15			15		4		0.01	4		30	
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			

* T_{Low} = - 55°C for **HCC** device : - 40°C for **HCF** device.

* T_{High} = + 125°C for **HCC** device : + 85°C for **HCF** device.

The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

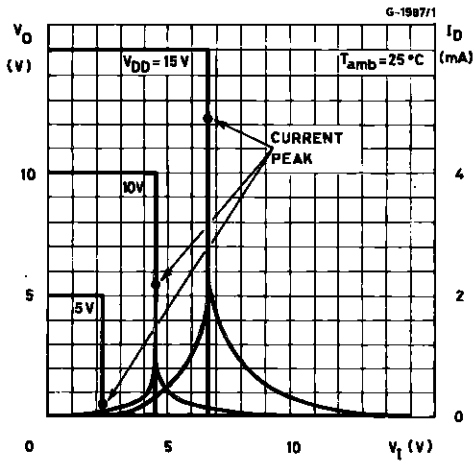
STATIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions				Value						Unit	
		V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V
			9/1	< 1	10		3			3		3	
			13.5/1.5	< 1	15		4			4		4	
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36	
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9	
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4	
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1	
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36	
			0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9	
			0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4	
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA
			0/10	0.5		10	1.6		1.3	2.6		0.9	
			0/15	1.5		15	4.2		3.4	6.8		2.4	
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36	
			0/10	0.5		10	1.3		1.1	2.6		0.9	
			0/15	1.5		15	3.6		3.0	6.8		2.4	
I _{IH} , I _{IL}	Input leakage Current	HCC Types	0/18	Any Input	18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A
		HCF Types	0/15		15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1	
C _I	Input Capacitance		Any Input						5	7.5		pF	

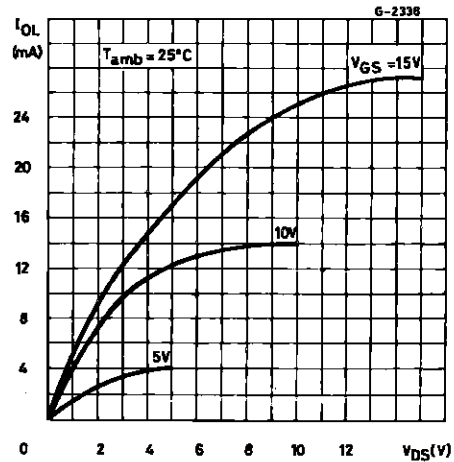
* T_{Low} = - 55°C for HCC device : - 40°C for HCF device.* T_{High} = + 125°C for HCC device : + 85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200k Ω , typical temperature coefficient for all V_{DD} values is 0.3%/°C, all input rise and fall times = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V _{DD} (V)	Min.	Typ.	Max.	
t _{PHL} , t _{PLH}	Propagation Delay Time		5		150	300	ns
			10		75	150	
			15		55	110	
t _{TLH} , t _{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

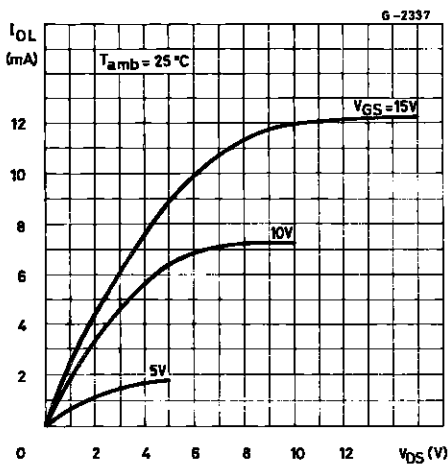
Typical Voltage and Current Transfer Characteristics.



Typical Output Low (sink) Current Characteristics.

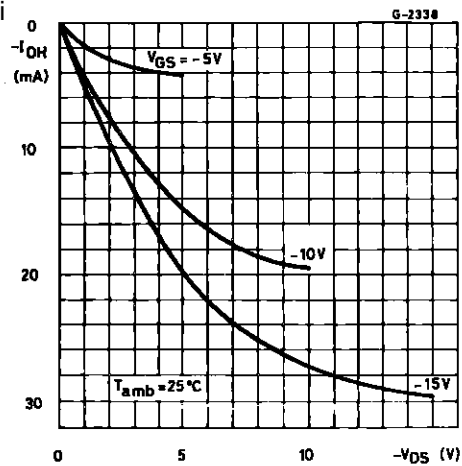


Minimum Output Low (sink) Current Charac-

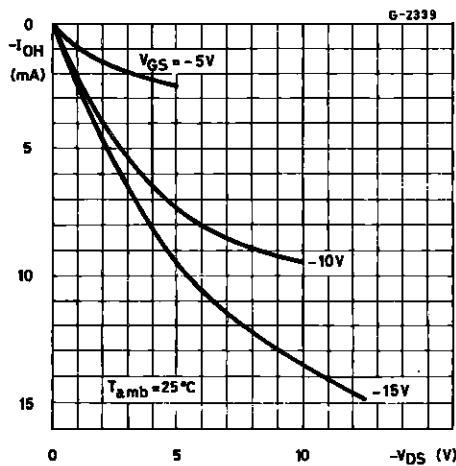


teristics.

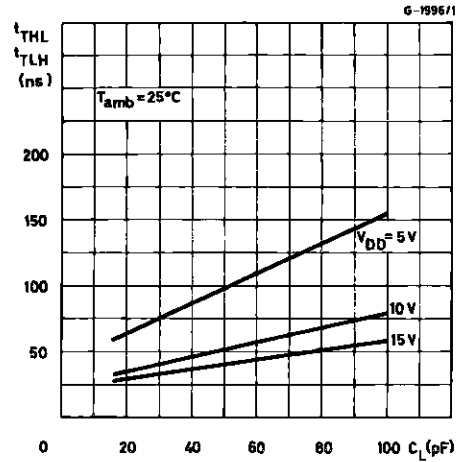
Typi



Minimum Output-p-channel Drain Characteristics.

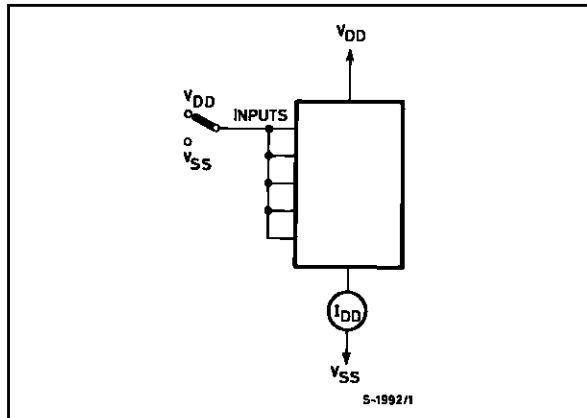


Typical Transition Time vs. C_L.

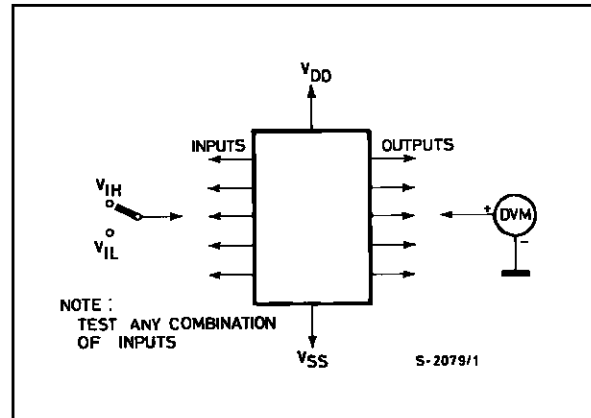


TEST CIRCUITS

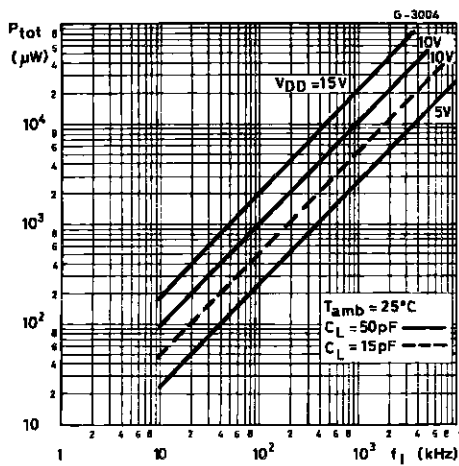
Quiescent Device Current



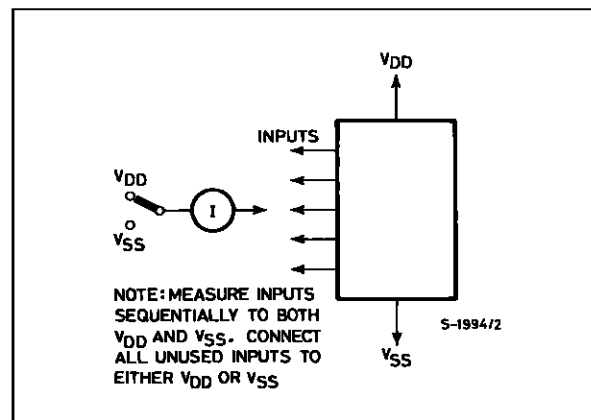
Input Voltage.



Typical Dynamic Power Dissipation vs. Frequency.

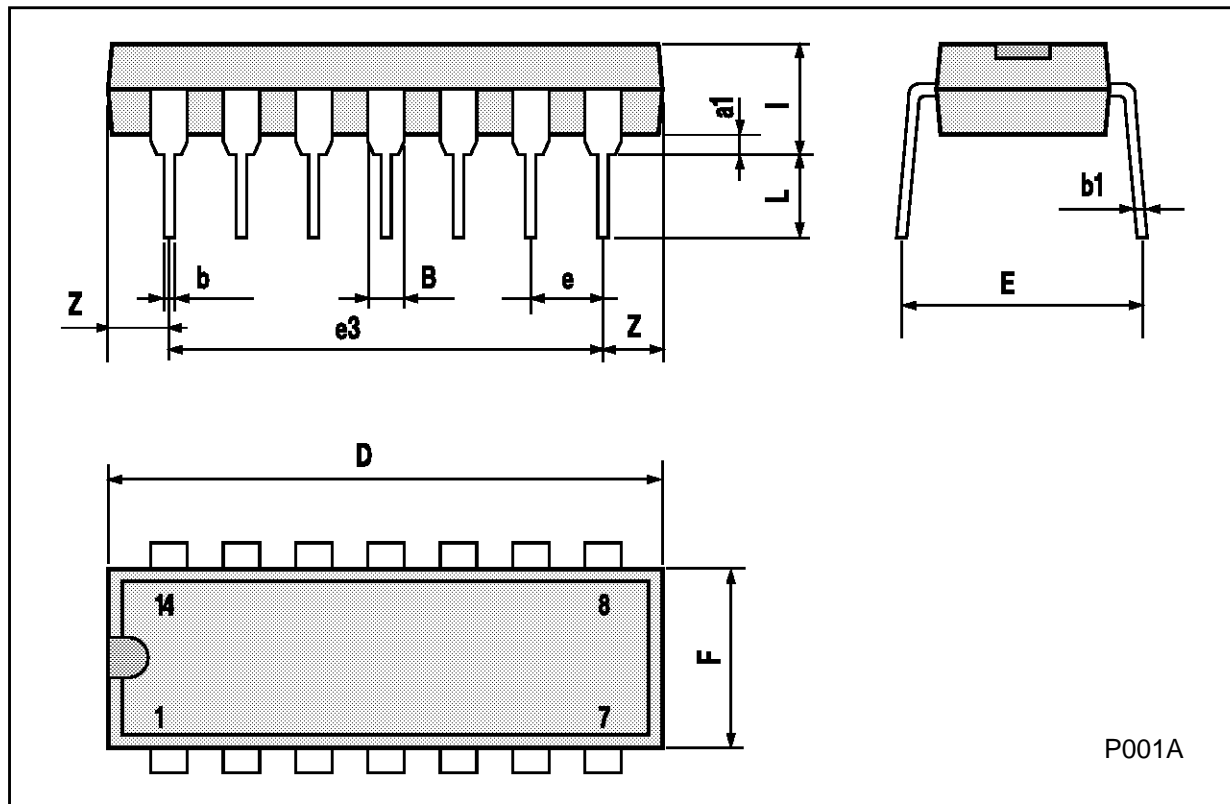


Input Current.



Plastic DIP14 MECHANICAL DATA

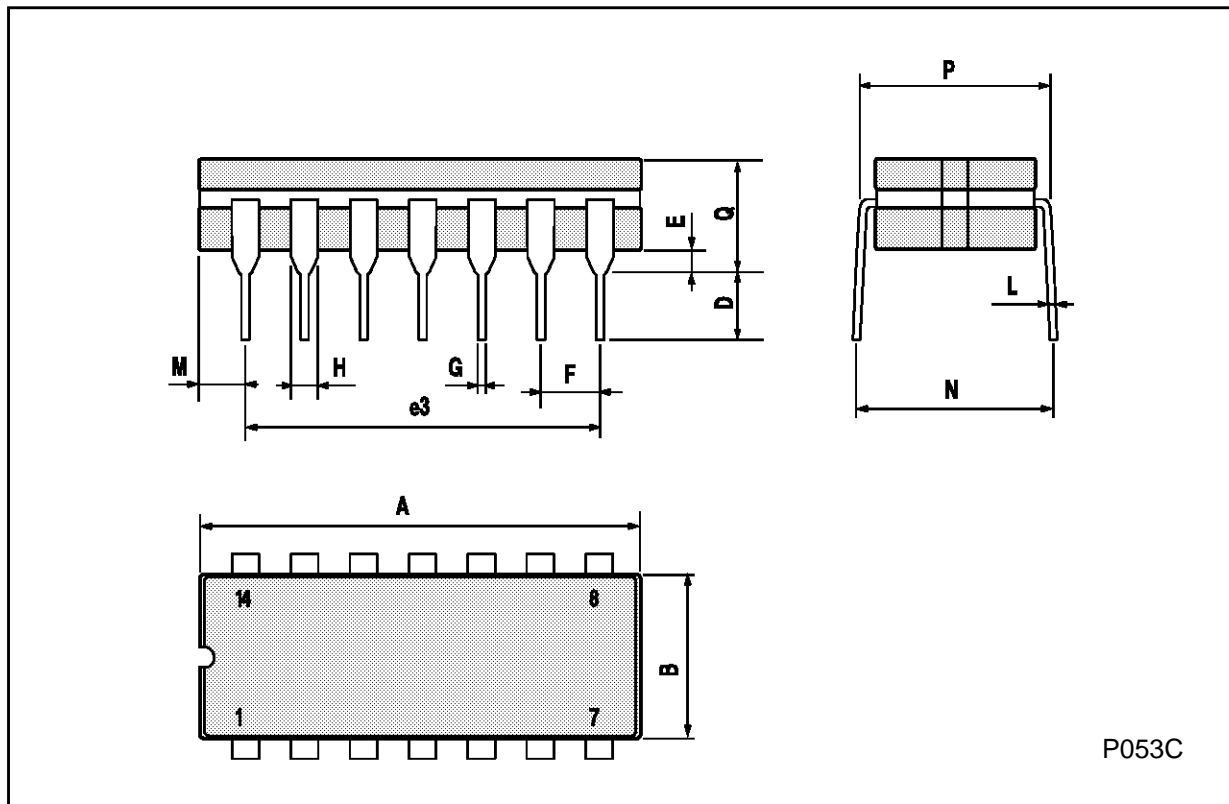
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



P001A

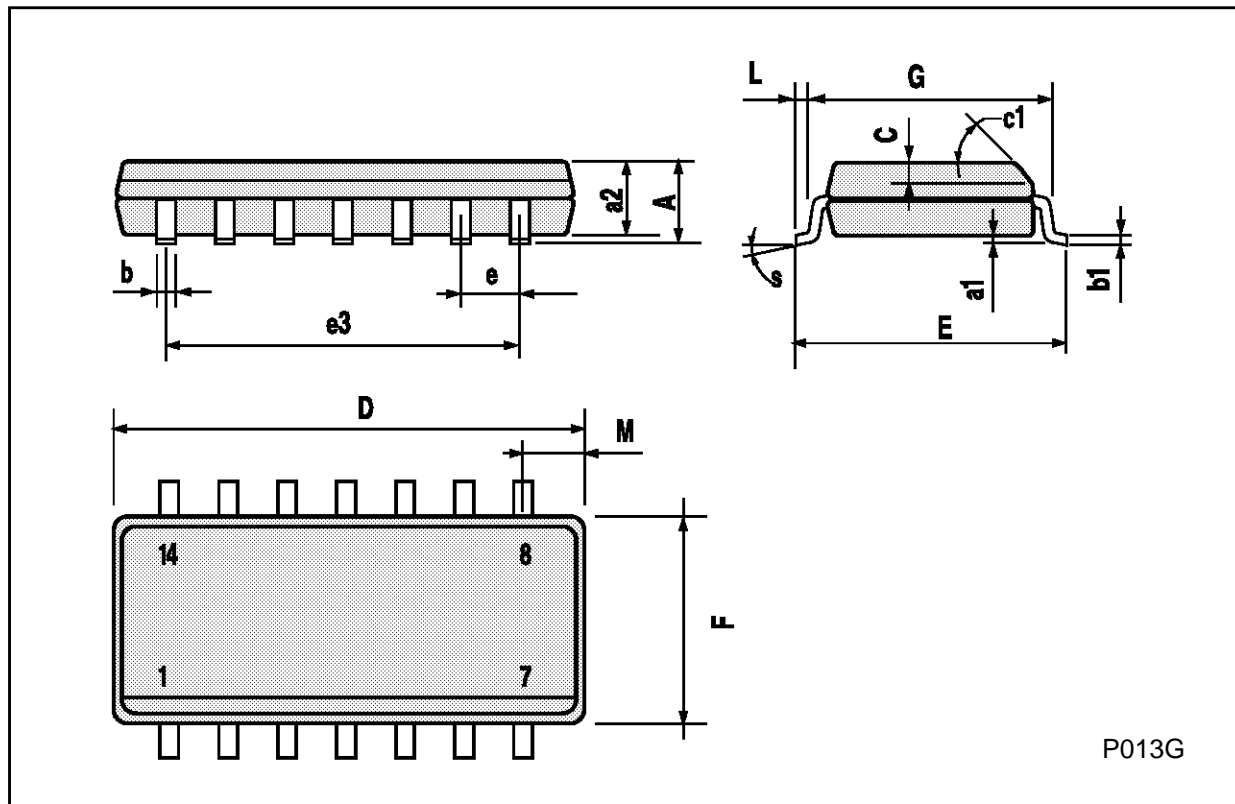
Ceramic DIP14/1 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7.0			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		15.24			0.600	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	1.52		2.54	0.060		0.100
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



SO14 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



P013G

PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



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